	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment s
1	BRS	L1	15	lowther near rex.in.	USPA T; US-P GPUB; EPO; DERW ENT; IBM_ TDB	2004/01/0 2 14:21	
2	BRS	L2	: La / I	young near william.in.	USPA T; US-P GPUB ; EPO; DERW ENT; IBM_ TDB	2004/01/0 2 14:23	
3	BRS	L3	123	(current near path\$1) near25 (symmetr\$3)	USPA T; US-P GPUB ; EPO; DERW ENT; IBM TDB	2004/01/0 2 14:28	
4	BRS	L4	5185	(current) near25 (symmetr\$3)	USPA T; US-P GPUB ; EPO; DERW ENT; IBM TDB	2004/01/0 2 14:29	

	Туре	L #	Hits	Search Text	DBs	Time Stamp	Comment s
5	BRS	L5	5		USPA T; US-P GPUB; EPO; DERW ENT; IBM_ TDB	2004/01/0 2 14:30	
6	BRS	L6	64	(current) near25 (symmetr\$3) near25 (shield\$3)	USPA T; US-P GPUB ; EPO; DERW ENT; IBM_ TDB	2004/01/0 2 14:30	

	U	1	PT	P	Document ID	Issue Date	Pages	Title
1					US 20030127686 A1	20030710	33	Symmetric inducting device for an integrated circuit having a ground shield
2	☒				US 20020085320 A1	20020704		AP-pinned spin valve design using very thin Pt-Mn AFM layer
3					US 6635949 B2	20031021	28	Symmetric inducting device for an integrated circuit having a ground shield
4					US 6473277 B1	20021029	14	Read head with leads to shields shorts for permitting a thinner second read gap layer and improving read signal symmetry
Ŋ				1	US 20030127686 A	20031021	28	Symmetric inducting device for integrated circuit, has shield between substrate second surface and main metal layer, and being patterned into segments that are symmetric at a plane of symmetry